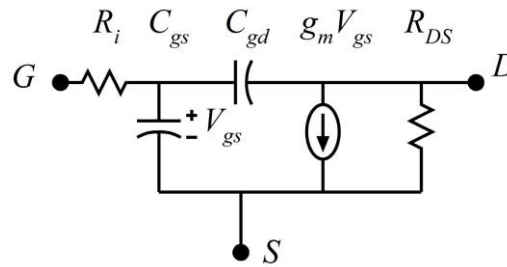


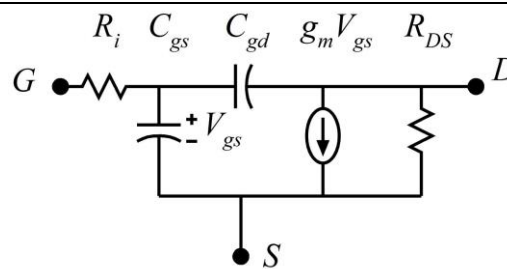
ECE 145a /218A problem set (device models, 2 port parameters, impedance matching). Note: please download the ADS directory ADS_for_218a, unarchive this in ADS, and use this for the simulation portion of the assignment.

Problem 1: Shown is a highly simplified small-signal model of a MOSFET. $R_i=0$ Ohms, $g_m=50$ mS, $R_{ds}=200$ Ohms, $C_{gs}=30$ fF, $C_{gd}=0$ fF. The source is grounded.



- Compute by hand the four Y-parameters as a function of frequency.
- create a 2-port circuit of this device in ADS. Simulate using the provided gain_testbench, and make plots of the real and imaginary parts of the 4 Y-parameters. Use linear scales for both axes.

Problem 2 (**218A only**): Now set . $R_i=10$ Ohms, $g_m=50$ mS, $R_{ds}=200$ Ohms, $C_{gs}=30$ fF, $C_{gd}=0$ fF. The source is grounded.



- Again compute the 4 Y-parameters (real and imaginary parts) by hand. Use numerical approximations so that all four of these are written as polynomials in $(j\omega)^n$, and truncate the polynomials to 2nd order in $(j\omega)$. Comment about how the effects of the various circuit elements show up in the Y parameters.

- Again simulate using the provided gain_testbench, and make plots of the real and imaginary parts of the 4 Y-parameters.

This is an elementary introduction to device model extraction: S-parameters are measured of a transistor, converted to Y-parameters, and compared to that of a model.

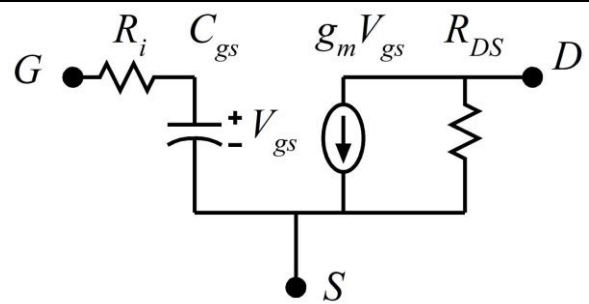
Problem 3 (**218A only**): Take. R_i , g_m , R_{ds} , C_{gs} , and C_{gd} as algebraic variables. Compute the 4 Y-parameters (real and imaginary parts) by hand. Use numerical approximations so that all four of these are written as polynomials in $(j\omega)^n$, and truncate the polynomials to 2nd order in $(j\omega)$.

In this derivation, assume that $\omega R_i C_{gs}$ and $\omega R_i C_{gd}$ are both $\ll 1$. Comment about how the effects of the various circuit elements show up in the Y parameters, and how the measured transistor Y-parameters could be used to determine the equivalent circuit element values.

Problem 3: $R_i=0$ Ohms, $g_m=50$ mS, $R_{ds}=200$ Ohms, $C_{gs}=30$ fF, $C_{gd}=0$ fF . The source is grounded.

a) Compute by hand the four S-parameters. Make a hand sketch of dB magnitude of S11 and S21 vs frequency on a log scale (DC-300 GHz)

b) Simulate using the provided gain_testbench, and make plots of dB magnitude of S11 and S21 vs frequency (DC-300 GHz) on a log scale

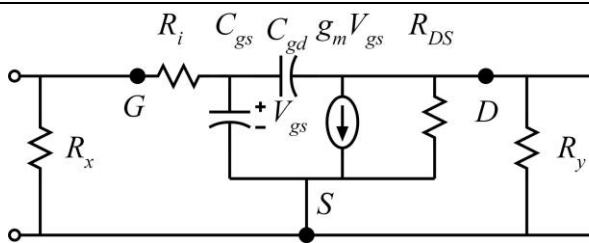


Please also make plots on the Smith chart of S11 and S22, and polar plots of S21 and S12.

Problem 4: **(please DO work this problem)** Simple common-source amplifier (bias networks are not shown) $R_i=0$ Ohms, $g_m=50$ mS, $R_{ds}=200$ Ohms, $C_{gs}=30$ fF, $C_{gd}=0$ fF

a) Compute the values of R_x and R_y necessary to give 50 Ohm input and output impedance *at low frequencies*.

(b) the circuit is then to be used in a 50 Ohm system, i.e. with 50 Ohm generator and load. Compute by hand all four S-parameters.



(c) Explain precisely how S11, S22, S21 relate to gain, input and output impedance.

(d) Simulate using the provided gain_testbench, and make plots of dB magnitude of all 4 S-parameters vs frequency (DC-300 GHz) on a dB and log frequency scale.